L Number	Hit	Sear h Text	DB	Time stamp
-	1006	235/494.ccls.	USPAT; US-P PUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:55
-	0	235/494.ccls. and chiba.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:56
-	0	jp-223380-$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:56
-	9	"223380"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:57
-	0	jp-223380-$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:58
-	0	jp-5923512-$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 17:58
-	2	jp-2000223380-$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:00
-	0	jp-2175154-$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:00
-	1	jp-3116919-$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:00
-	15423	chiba.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:02

-	818	chiba.in. and semiconduct r	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:02
-	58	(chiba.in. and semic nductor) and mark	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:05
-	153	(chiba.in. and semiconductor) and wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:06
-	83	235/494.ccls. and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:10
-	8	(235/494.ccls. and semiconductor) and wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:06
-	34	(235/494.ccls. and semiconductor) and mark	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 18:47
-	2	6305677.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:16
-	174	269/13.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:18
-	81423	semiconductor adj2 wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:19
-	4744	(semiconductor adj2 wafer) and mark	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:19

-	4500	((semi nductor adj2 waf r) and mark) and (semi nduct r adj waf r)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:20
-	61	(((s mic ndu tor adj2 wafer) and mark) and (semiconductor adj wafer)) and reproduce	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 18:53
-	22	semiconductor adj mark	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 18:52
-	1602	355/53.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:29
-	1154	355/53.ccls. and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:29
-	1052	(355/53.ccls. and semiconductor) and wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:29
-	415	((355/53.ccls. and semiconductor) and wafer) and mark	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:30
-	8	(((355/53.ccls. and semiconductor) and wafer) and mark) and reproduce	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:32
-	0	(((355/53.ccls. and semiconductor) and wafer) and mark) and efface	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:32
-	5	(((355/53.ccls. and semiconductor) and wafer) and mark) and erase	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:34

		0	(((355/53.ccls. and semiconduct r) and wafer) and mark) and (repr duc adj erased adj marks)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:35
-		0	((((355/53. cls. and semiconductor) and wafer) and mark) and (reproduce erased marks)) and efface	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:35
-		10	((((355/53.ccls. and semiconductor) and wafer) and mark) and (reproduce erased marks)) and notch	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:35
-		300	(((355/53.ccls. and semiconductor) and wafer) and mark) and (reproduce erased marks)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:38
-		0	(((355/53.ccls. and semiconductor) and wafer) and mark) and (reproduce near erased near marks)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:39
-		0	(((355/53.ccls. and semiconductor) and wafer) and mark) and (reproduce same erased same marks)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:39
-		121	(((355/53.ccls. and semiconductor) and wafer) and mark) and identical	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:40
-		9	((((355/53.ccls. and semiconductor) and wafer) and mark) and identical) and reproduce$2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:44
-		172	(((355/53.ccls. and semiconductor) and wafer) and mark) and prevent	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:44
-		3	((((355/53.ccls. and semiconductor) and wafer) and mark) and prevent) and erase	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:53

-	354	355/43.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:53
-	84	355/43.ccls. and s miconduct r	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:53
-	71	(355/43.ccls. and semiconductor) and wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:53
-	1	(((355/43.ccls. and semiconductor) and wafer) and mark) and erase	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:54
-	45	((355/43.ccls. and semiconductor) and wafer) and mark	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:58
-	25968	355/$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:58
-	2116	355/$.ccls. and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:59
-	1469	(355/$.ccls. and semiconductor) and wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:59
-	497	((355/$.ccls. and semiconductor) and wafer) and mark	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:59
-	8	(((355/$.ccls. and semiconductor) and wafer) and mark) and erase	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 18:59

-		13	(((355/$.ccls. and semi ndu t r) and wafer) and mark) and r pr duce	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 19:02
-		1	((((355/$. cls. and semic nduct r) and wafer) and mark) and erase) and ((((355/$.ccls. and semiconductor) and wafer) and mark) and reproduce)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/30 19:02
-		6	(235/494.ccls. and semiconductor) and mark and duplicate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 18:51
-		0	(235/494.ccls. and semiconductor) and (duplicate adj mark)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 18:51
-		3	(235/494.ccls. and semiconductor) and (duplicate same mark)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 18:51
-		0	(semiconductor adj mark) same duplicate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 18:53
-		0	((((semiconductor adj2 wafer) and mark) and (semiconductor adj wafer)) and reproduce) and (duplicate same mark)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 18:53
-		0	((((semiconductor adj2 wafer) and mark) and (semiconductor adj wafer)) and reproduce) and (duplicate near mark)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 18:53
-		0	((((semiconductor adj2 wafer) and mark) and (semiconductor adj wafer)) and reproduce) and (duplicate adj mark)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 18:53
-		72	(((semiconductor adj2 wafer) and mark) and (semiconductor adj wafer)) and reproduce	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 18:54

-	3	((((semiconduct r adj2 waf r) and mark) and (semiconduct r adj wafer)) and repr duce) and duplicate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/09 18:54
-	26645	355/$. ls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/10 12:08
-	102	430/13.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/10 12:09
-	435	257/620.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/10 12:09
-	1104	235/494.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/30 12:08
-	27013	355/$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/30 12:08
-	462	257/620.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/30 12:09
-	104	430/13.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/30 12:09
-	1015	replace same mark	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/30 12:09
-	99	(replace same mark) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/30 12:12

-	3	((replace same mark) and semic nductor) and 235/$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/30 12:14
-	89611	semicondu tor adj wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/30 12:19
-	5456	(semiconductor adj wafer) and mark	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/30 12:20
-	2	((semiconductor adj wafer) and mark) and (replace near10 mark)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/30 12:20